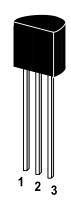
## **ST 2SC1740** 查询"2SC1740"供应商

#### **NPN Silicon Epitaxial Planar Transistor**

for switching and AF amplifier applications.

The transistor is subdivided into four groups Q, R, S and E. according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

#### Absolute Maximum Ratings ( $T_a = 25^{\circ}C$ )

	Symbol Value		Unit
Collector Base Voltage	V <sub>CBO</sub>	60	V
Collector Emitter Voltage	V <sub>CEO</sub>	50	V
Emitter Base Voltage	V <sub>EBO</sub>	5	V
Collector Current	I <sub>C</sub>	150	mA
Power Dissipation	P <sub>tot</sub>	300	mW
Junction Temperature	Tj	T <sub>j</sub> 150	
Storage Temperature Range	Ts	-55 to +150	°C







Dated : 07/12/2002

### **ST 2SC1740** 查询"2SC1740"供应商

# Characteristics at $T_{amb}$ =25 $^{\circ}C$

		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at V <sub>CE</sub> =6V, I <sub>C</sub> =1mA	Q	h <sub>FE</sub>	120	-	270	-
	R	h <sub>FE</sub>	180	-	390	-
	S	h <sub>FE</sub>	270	-	560	-
	Е	h <sub>FE</sub>	390	-	820	-
Collector Base Breakdown Voltage						
at I <sub>C</sub> =50μA		V <sub>(BR)CBO</sub>	60	-	-	V
Collector Emitter Breakdown Voltage						
at I <sub>c</sub> =1mA		V <sub>(BR)CEO</sub>	50	-	-	V
Emitter Base Breakdown Voltage						
at I <sub>E</sub> =50μA		$V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current						
at V <sub>CB</sub> =60V		I <sub>CBO</sub>	-	-	0.1	μΑ
Emitter Cutoff Current						
at V <sub>EB</sub> =5V		I <sub>EBO</sub>	-	-	0.1	μΑ
Collector Saturation Voltage						
at I <sub>C</sub> =50mA, I <sub>B</sub> =5mA		$V_{\text{CE(sat)}}$	-	-	0.4	V
Gain Bandwidth Product						
at $V_{CE}$ =12V, $I_C$ =2mA		f⊤	-	180	-	MHz
Output Capacitance						
at V <sub>CB</sub> =12V, f=1MHz		C <sub>OB</sub>	-	2	3.5	pF







Downloaded from Elcodis.com electronic components distributor

Dated : 07/12/2002